



ELT AO WFS Possible Developments

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- What detectors are required for ELT AO WFS?
- Specification highlights:
 - ⇒ LGS
 - ⇒ NGC
- Possible LGS Solutions
- Possible NGS Solutions
- Development Plan/Schedule
- Summary





- Two types of detectors have been identified:
 - ⇒ LGS WFS detector: very large pixel format to sample spot elongation, high frame rate (700 Hz), and low noise (<3e).</p>
 - ⇒ XAO WFS detector: for a pyramid WFS, 256² pixels are sufficient, but extremely high frame rate (3 to 4 kHz) and very low noise (~1 e).
- Assumed 5.5 years to develop (2008-2013) thus must be based on almost available technology
- Detector requirements differ sufficiently to believe separate development are required
- Concentrated so far on LGS WFS detector
 - ⇒ as thought to be the most challenging and
 - ⇒ Critical for the success of the ELT.
 - ⇒ Highest priority for ESO



LGS Specifications highlights

- **OP** Current LGS WFS baselines:
 - Up to 6 Sodium LGSs (= 589 nm)
 - Spatial sampling of <u>84 x 84 sub-apertures</u> (goal 100 x 100)
 - Sample the spot elongation by <u>20 x 20 pixels</u> per sub-aperture
 - Large <u>pixels 24-50um</u>, small full well < 4000e</p>
 - 100% fill for maximum flexibility
 - High temporal sampling of <u>700 Hz</u>
 - High <u>QE > 90%</u>
 - Low <u>RON < 3e- (goal <1 e-)</u>, DC < 0.5e/pix/frame</p>
 - Good spatial <u>PSF of 0.8pixel</u>
 - Handle pulsed lasers (several pulses per int. time)
 Non-destructive electronic shuttering
 - ⇒Noiseless addition of charge from laser pulses
 - Ease of use/compact size:
 - ⇒Integrated Read-Out electronics
 - ⇒Simple (if possible digital) industry std interface
 - ⇒Goal: data compress by performing centroid on-chip
 - ⇒Peltier cooling
 - Goal: Extension to first light NGS WF Sensing



Image seen by a ¹/₄ detector at the focal plane of the WFS



XAO Specifications highlights



- XAO Pyramid wavefront sensing
- Spatial sampling of <u>200 x 200 sub-apertures</u>
- 4 quadrant detection (separate detectors) of 200x200 pixels
- Large <u>pixels 24-50um</u>, small full well < 4000e</p>
- Very High temporal sampling of <u>3-4 kHz</u>
- High <u>QE > 90%</u> (450-1000nm) especially into the <u>RED</u>
- Low <u>RON < 1e-</u>, DC << 0.1e/pix/frame</p>
- Good spatial of <u>PSF 0.8pixel</u>
- Ease of use/compact size:
 - ⇒Integrated Read-Out electronics
 - ⇒Simple interface
 - ⇒Peltier cooling





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Performed Design Studies to Get Answers





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VLT PROGRAMME



VLT PROGRAMME

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TELESCOPE SYSTEMS DIVISION

ELT Visible Adaptive Optics WFS Detector Conceptual Design Study Statement of Work

TELESCOPE SYSTEMS DIVISION

ELT Visible Adaptive Optics WFS Detector Technical Specifications

Milestones	Date (months)	Deliverables
Milestone 1: Start contract	То	Contract signature and Kick-Off Meeting Minutes of KO meeting
Milestone 2: Straw-Man Design Report	To + 2	Report one week before meeting Straw-man Design Report and Progress Meeting
Milestone 3: Design Review	To + 6	Detector Conceptual Design Study Report Review Meeting 4 weeks later Minutes of Design Review Meeting

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Lots of options studied but discarded!



Discarded:

- HyViSi
- 3-D integrated FPA (MIT/LL)
- CCD/CMOS with charge detection in CMOS
- CCD/CMOS with charge detection in CCD
- CMOS Mosaic
- CCD Mosaic
- CMOS/CMOS hybrid
- pnCCDs Mosaic

<u>Reasons:</u>

- Not able to reach read noise and/or require cooling to low 70K temperatures
- ⇒ Serious trades between parameters; noise, power dissipation, latency and read out speed
- ⇒ Too complex and/or manufacturability issues
- ⇒ Technology immature.

	Front Side	Hybrid	3D	Backside
QE				
Dark Current				
Noise				
100% Operability				
Size/Stitching				
VLSI capability				
Manufacturability				

ELT AO WFS Possible



The Survivors



Monolithic CMOS

 Front-Side Illuminated (FSI)
 Back-side Illuminated (BSI)

 Orthogonal Transfer CCD
 APD/CMOS Hybrid

Note that ESO has signed NDA agreements and is limited to amount of detail that can be shown.



Monolithic CMOS



Use novel pixel designs that:

- Pin the photodiode to reduce dark current to make just below zero operation possible
- Build a CCD into the pixel to
 - ⇒ Noiselessly sample multiple laser pulses,
 - Decouple the photodiode capacitance for high conversion gain (and low noise) and good linearity
 - ⇒ enables true DCS
- Build from large transistors to reduce occurrence of RTS noise
- Do DCS within the pixel to circumvent trade between read out speed and signal analog processing time.
- Do on-chip digitization for simple digital interface
- Do LVDS for glueless interface to FPGA (e.g. Xilinx)





FSI Monolithic CMOS



Incident

- Use advanced techniques to improve QE:
 - ⇒ Gapless micro lenses (100% pixel fill) to overcome problem of structures inside the pixel
 - ⇒ Optical light pipes through interlayer dielectrics
- Low risk first step with current technology
- Drawbacks are behavior of the microlens array, but their quality is improving fast and QE of ~ 80% estimated.









BSI Monolithic CMOS



 Although technology is very new specifications can almost already be met today

- ⇒ QE> 80% from 450 –850 nm
- ⇒ Dark current 14pA/cm2
- BSI CMOS will become the technology for Mobile Phone Cameras. At pixel size of <1.2um backside illumination will be cheaper
 - Compared to light piping or buried ulens
 - Many CIS foundries/fabs are working on backside illumination
- We could benefit from this technology development



[Bogaerts] J. Bogaerts, K. De Munck, P. De Moor, D. Sabuncuoglu Tezcan, I. Ficai Veltroni, G. Lepage, C. Van Hoff, "Radiometric Performance Enhancement of Hybrid and Monolithic Backside Illuminated CMOS APS for Space –borne Imaging", 2007 International Image Sensor Workshop



Pixel Size Roadmap (from Micron Technologies)

Orthogonal Transfer CCD



- Read out X/Y profile rather than the whole image.
- After each half integration time transfer and bin charge in X or Y.
- Data compression of ~ 10 (20pixels/2 samples of X and Y).
- Add integral pixel electronic shutter:
 - ⇒ shutter drain competes with pixel electrode for collection of charge
- Use electron multiplication for output; < 1e RON



Orthogonal Transfer CCD Considerations



Pros:

- 10 times data compression
- reduce amplifier count to comparative manageable number
- Signal is summed (binned) thus improvement in S/N; more signal per binned pixel but same RON.
- Less data and in 1D form so less processing in the RTC

Cons:

- Half of the light is effectively lost since the frame rate must be doubled to 1.4KHz
- Excess noise → effective QE is halved
- Binning adds dark current of pixels
- Sky noise added to LGS image through the binning process
- Some loss of structural information in the LGS image
- Less flexible as fill factor < 100%</p>
- Large number of electron multiplication outputs still need to be demonstrated



Orthogonal Transfer CCD Simulations





Early simulation results:

At expected LGS signal ~ 150-200e per subaperture, 0.1e RON orthogonal CCD performs as good as a 3e RON conventional detector.

Additional work:

- ⇒ Optimize the centroid computation.
- ⇒ Simulate full system rather than consider only the sub-aperture.
- Could be a good backup plan.

APD/CMOS Hybrid







Low voltage < 6V

- Backthinned Avalanche Photo Diode Array hybridized to a CMOS (0.18um) detection/thresholder/counter read out.
- Modest APD gain of ~ 100-200, low voltage < 6V
- Photon counter within the pixel by thresholding single events and incrementing a counter.
- Simple shuttering by resetting and enabling the counter.
- Simple digital (e.g. LVDS) output interface
- Low pin connections: Master clock, 3V3 power/gnd, APD bias (-10V), and shutter/read out synchronizing signals.



Centroid Processor Off-Chip



- All design studies recommended to do centroiding off-chip.
 - ⇒ Power dissipation, noise cross-talk and too high risk quoted as main reasons
- FPGAs identified as good design platform with minimal glue logic to sensor.
- Requirements are challenging:
 - ⇒ 125GFlops (19.6Mflops per sub-aperture), the total memory 102MB (16kB per sub-aperture), and the external data bandwidth 170Mbyte/s.
 - ✓ 20 words (40 bytes) of memory per pixel
 - ✓ 70 integer/floating point operations per pixel per read out frame
 - Receive 4 floating point/integer parameters (e.g. pixel weighting, sodium layer profile information) per pixel every second
 - Transmit X and Y centroid, a measure of the image sharpness, and the intensity ΣxΣy lx,y per subaperture per read out frame
 - Transmit raw 10 times a second for model updating and diagnostic purposes.
 - ✓ Achieve Centroid Calculation Latency < 100µs per subaperture</p>







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Take 264x264 pnCCD



4 output nodes



QE pnCCD First Test Run



- Too small for LGS detector!
- 264x264 51um pixel
- 450um thick
- Split frame transfer
- One output amplifier per column
- Total 528 amplifiers
- 1000 fps
- RON < 3e</p>
- Integrated with CAMEX
 - ⇒ Gain
 - ⇒ Analog DCS signal processing
 - ⇒ Multiplexing of 132 channel to 1 output







- See talk "AA-pnCCD detector development plan Henk Spruit"
- Question: Can the AA-pnCCD be sped up to 3kfps?







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LGS Development Plan



- Most of the solutions for the LGS detector are almost there separately but will require a technology validation phase where existing components are put together and some interesting new concepts/ideas are explored.
- Technology validation phase will consist of two steps (biggest risks first) :
 - Pixel Design Demonstrator (PD) where several pixel designs and geometries are tested to optimize read noise, high speed operation, shutter extinction, APD gain, bump bond yield etc.
 - Scaled-Down Demonstrator (SDD) where chip architecture is proved. A device will be developed that functions similar (with ADCs, multiplexing logic and output LVDS interface) to the final unit but of a smaller size (and lower cost).

Full Scale Demonstrator

⇒ Manufacture full size device (identical to final) meeting all specifications

Testing and Acceptance

⇒ Verify performance and give the go ahead to manufacture the final devices

Production Phase

⇒ Up to 30 final devices are manufactured















- Two types of AO WFS detectors identified for ELT:
 - ⇒ LGS WFS detector: 1600x1600pixels, 700 frame/sec, and low noise (<3e).</p>
 - ⇒ XAO WFS detector: 255x256pixels, 3-4 kframe/sec, and very low noise (~1 e)
- Requirements for LGS detector are most challenging but constituents of several solutions almost exist:
 - ➡ Monolithic CMOS
 - ⇒ <u>APD/CMOS Hybrid</u>
 - ➡ Orthogonal Transfer CCD
- Development plan broken down into several phases will allow progressive retirement of risk at the earliest opportunity (largest ones first) and guarantee final success.







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